



PNP MJ4030 – MJ4031 – MJ4032

MEDIUM POWER COMPLEMENTARY SILICON TRANSISTORS

They are silicon epitaxial-base PNP power transistors in monolithic Darlington configuration and are mounted in Jedec TO-3 metal case.

They are intended for use as output devices in complementary general purpose amplifier applications.

The complementary NPN types are the MJ4033, MJ4034, MJ4035

Compliance to RoHS

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit	
V_{CBO}	Collector-Base Voltage	$I_E=0$	MJ4030	-60	V
			MJ4031	-80	
			MJ4032	-100	
V_{CEO}	Collector-Emitter Voltage	$I_B=0$	MJ4030	-60	V
			MJ4031	-80	
			MJ4032	-100	
V_{EBO}	Emitter-Base Voltage	$I_C=0$	MJ4030	-5.0	V
			MJ4031		
			MJ4032		
I_C	Collector Current		-16	A	
I_B	Base Current		-0.5	A	
P_T	Power Dissipation	@ $T_C < 25^\circ$	150	W	
T_J	Junction Temperature		200	°C	
T_s	Storage Temperature		-65 to +200		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R_{thJ-C}	Thermal Resistance, Junction to Case	1.17	°C/W

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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

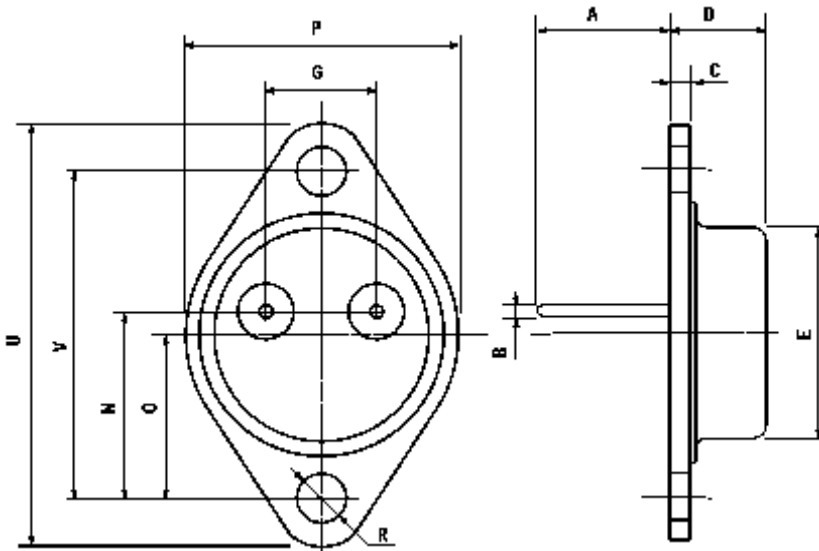
Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
V_{CEO}	Collector-Emitter Voltage (*)	$I_C = -100 \text{ mA}, I_B = 0$	MJ4030	-60	-	-	V
			MJ4031	-80	-	-	
			MJ4032	-100	-	-	
I_{CEO}	Collector Cutoff Current	$V_{CE} = -30 \text{ Vdc}, I_B = 0$	MJ4030	-	-	-3.0	mA
		$V_{CE} = -40 \text{ Vdc}, I_B = 0$	MJ4031	-	-		
		$V_{CE} = -50 \text{ V}, I_B = 0$	MJ4032	-	-		
I_{EBO}	Emitter Cutoff Current	$V_{BE} = -5.0 \text{ V}, I_C = 0$	MJ4030	-	-	-5.0	mA
			MJ4031	-	-		
			MJ4032	-	-		
I_{CER}	Collector-Emitter Leakage Current	$V_{CB} = -60 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$	MJ4030	-	-	-1.0	mA
		$V_{CB} = -80 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$	MJ4031	-	-		
		$V_{CB} = -100 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$	MJ4032	-	-		
		$V_{CB} = -60 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$ $T_C = 150^\circ\text{C}$	MJ4030	-	-	-5.0	
		$V_{CB} = -80 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$ $T_C = 150^\circ\text{C}$	MJ4031	-	-		
		$V_{CB} = -100 \text{ V}$ $R_{BE} = 1.0 \text{ k}\Omega$ $T_C = 150^\circ\text{C}$	MJ4032	-	-		
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -10 \text{ A}$ $I_B = -40 \text{ mA}$	MJ4030	-	-	-2.5	V
			MJ4031	-	-		
			MJ4032	-	-		
		$I_C = -16 \text{ A}$ $I_B = -80 \text{ mA}$	MJ4030	-	-	-4.0	
			MJ4031	-	-		
			MJ4032	-	-		
V_{BE}	Base-Emitter Voltage (*)	$I_C = -10 \text{ A}$ $V_{CE} = -3.0 \text{ V}$	MJ4030	-	-	-3	V
			MJ4031	-	-		
			MJ4032	-	-		
h_{FE}	DC Current Gain (*)	$V_{CE} = -10 \text{ V}$ $I_C = -3.0 \text{ A}$	MJ4030	1000	-	-	-
			MJ4031				
			MJ4032				

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 2.0\%$

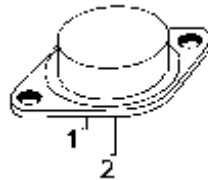
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MECHANICAL DATA CASE TO-3

DIMENSIONS (mm)		
	min	max
A	11	13.10
B	0.97	1.15
C	1.5	1.65
D	8.32	8.92
F	19	20
G	10.70	11.1
N	16.50	17.20
P	25	26
R	4	4.09
U	38.50	39.30
V	30	30.30



Pin 1 :	Base
Pin 2 :	Emitter
Case :	Collector



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